# Low-Voltage CMOS Quad 2-Input OR Gate

# With 5 V-Tolerant Inputs

The MC74LCX32 is a high performance, quad 2–input OR gate operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A  $V_{\rm I}$  specification of 5.5 V allows MC74LCX32 inputs to be safely driven from 5.0 V devices.

Current drive capability is 24 mA at the outputs.

#### **Features**

- Designed for 2.3 V to 3.6 V V<sub>CC</sub> Operation
- 5.0 V Tolerant Inputs Interface Capability With 5.0 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V

Machine Model >200 V

• Pb-Free Packages are Available\*

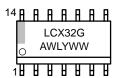


http://onsemi.com

MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A

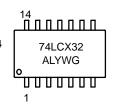




TSSOP-14 DT SUFFIX CASE 948G







A = Assembly Location

L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb−Free Package
■ Pb−Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

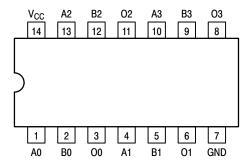


Figure 1. Pinout: 14-Lead (Top View)

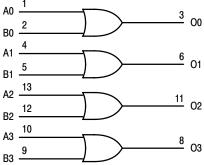


Figure 2. Logic Diagram

#### **PIN NAMES**

Pins	Function
An, Bn	Data Inputs
On	Outputs

#### **TRUTH TABLE**

Inp	outs	Outputs
An	Bn	On
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

H = High Voltage Level L = Low Voltage Level

For I<sub>CC</sub> reasons, DO NOT FLOAT Inputs

### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Condition	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State.(Note 1)	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
		+50	V <sub>O</sub> > V <sub>CC</sub>	mA
I <sub>O</sub>	DC Output Source/Sink Current	±50		mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±100		mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

<sup>1.</sup> I<sub>O</sub> absolute maximum rating must be observed.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Par	ameter	Min	Туре	Max	Unit
V <sub>CC</sub>	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
Vo	Output Voltage	(HIGH or LOW State) (3-State)	0		V <sub>CC</sub>	V
I <sub>OH</sub>	HIGH Level Output Current	V <sub>CC</sub> = 3.0 V - 3.6 V V <sub>CC</sub> = 2.7 V - 3.0 V V <sub>CC</sub> = 2.3 V - 2.7 V			-24 -12 -8	mA
l <sub>OL</sub>	LOW Level Output Current	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			+24 +12 +8	mA
T <sub>A</sub>	Operating Free-Air Temperature		-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate	, $V_{IN}$ from 0.8 V to 2.0 V, $V_{CC}$ = 3.0 V	0		10	ns/V

# DC ELECTRICAL CHARACTERISTICS

			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		
Symbol	Characteristic	Condition	Min	Max	Unit
V <sub>IH</sub>	HIGH Level Input Voltage (Note 1.)	2.3 V ≤ V <sub>CC</sub> ≤ 2.7 V	1.7		V
		2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V	2.0		
V <sub>IL</sub>	LOW Level Input Voltage (Note 1.)	2.3 V ≤ V <sub>CC</sub> ≤ 2.7 V		0.7	V
		2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V		0.8	
V <sub>OH</sub>	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ I}_{OH} = -100 \mu\text{A}$	V <sub>CC</sub> - 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.8		
		V <sub>CC</sub> = 2.7 V; I <sub>OH</sub> = -12 mA	2.2		
		V <sub>CC</sub> = 3.0 V; I <sub>OH</sub> = -18 mA	2.4		
		V <sub>CC</sub> = 3.0 V; I <sub>OH</sub> = -24 mA	2.2		
V <sub>OL</sub>	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V <sub>CC</sub> = 2.3 V; I <sub>OL</sub> = 8 mA		0.6	
		V <sub>CC</sub> = 2.7 V; I <sub>OL</sub> = 12 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 16 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 24 mA		0.55	
I <sub>I</sub>	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5	μΑ
Icc	Quiescent Supply Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$		10	μΑ
		$2.3 \le V_{CC} \le 3.6 \text{ V}; 3.6 \le V_{I} \text{ or } V_{O} \le 5.5 \text{ V}$		±10	
$\Delta I_{CC}$	Increase in I <sub>CC</sub> per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

<sup>1.</sup> These values of V<sub>I</sub> are used to test DC electrical characteristics only.

## AC CHARACTERISTICS $t_R = t_F = 2.5 \text{ ns}$ ; $R_L = 500 \Omega$

			Limits						
				$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$					
			V <sub>CC</sub> = 3.3	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 2.7 \text{ V}$ $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$					
			C <sub>L</sub> =	50 pF	C <sub>L</sub> =	50 pF	C <sub>L</sub> = 3	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub>	Propagation Delay Time	1	1.5	5.5	1.5	6.2	1.5	6.6	ns
t <sub>PHL</sub>	Input to Output		1.5	5.5	1.5	6.2	1.5	6.6	
toshl	Output-to-Output Skew			1.0					ns
toslh	(Note 2)			1.0					

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (toshL) or LOW-to-HIGH (toshH); parameter guaranteed by design.

#### **DYNAMIC SWITCHING CHARACTERISTICS**

			T <sub>A</sub> = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V <sub>OLP</sub>	Dynamic LOW Peak Voltage	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		8.0		V
	(Note 3)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		0.6		V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		-0.8		V
	(Note 3)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		-0.6		V

<sup>3.</sup> Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

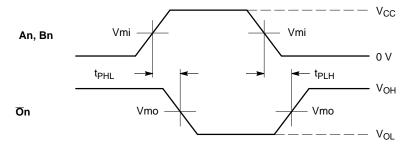
#### **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition	Typical	Unit
C <sub>IN</sub>	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	7	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	8	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, $V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	25	pF

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LCX32D	SOIC-14	55 Units / Rail
MC74LCX32DR2	SOIC-14	2500 Tape & Reel
MC74LCX32DR2G	SOIC-14 (Pb-Free)	2500 Tape & Reel
MC74LCX32DT	TSSOP-14*	96 Units / Rail
MC74LCX32DTG	TSSOP-14*	96 Units / Rail
MC74LCX32DTR2	TSSOP-14*	2500 Tape & Reel
MC74LCX32DTR2G	TSSOP-14*	2500 Tape & Reel
MC74LCX32MEL	SOEIAJ-14	2000 Tape & Reel
MC74LCX32MELG	SOEIAJ-14 (Pb-Free)	2000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. \*This package is inherently Pb-Free.

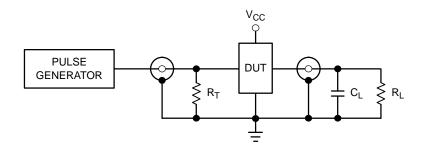


#### **WAVEFORM 1 - PROPAGATION DELAYS**

 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$ 

	Vcc				
Symbol	3.3 V <u>+</u> 0.3 V	2.7 V	2.5 V <u>+</u> 0.2 V		
Vmi	1.5 V	1.5 V	Vcc/2		
Vmo	1.5 V	1.5 V	Vcc/2		

Figure 3. AC Waveforms

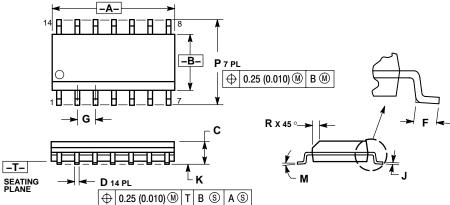


 $C_L=50$  pF at  $V_{CC}=3.3\pm0.3$  V or equivalent (includes jig and probe capacitance)  $C_L=30$  pF at  $V_{CC}=2.5\pm0.2$  V or equivalent (includes jig and probe capacitance)  $R_L=R_1=500~\Omega$  or equivalent  $R_T=Z_{OUT}$  of pulse generator (typically  $50~\Omega)$ 

Figure 4. Test Circuit

#### PACKAGE DIMENSIONS

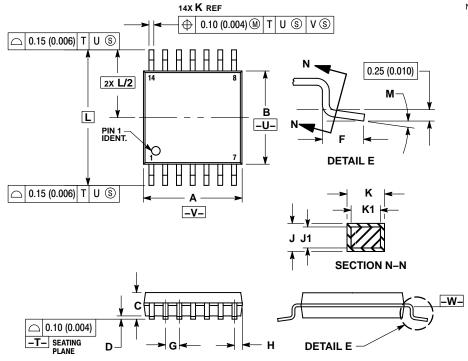
#### SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE G



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE
  DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.127
  (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE A** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  - 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL
- NOT EXCEED 0.25 (0.010) PER SIDE.

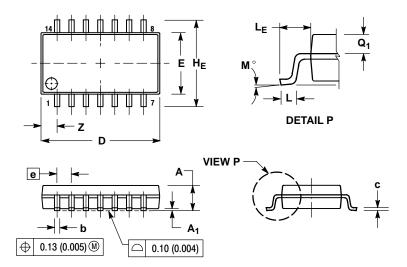
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
  DIMENSION AT MAXIMUM MATERIAL
- CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR
- DETERMINAL NOMBERS ARE SHOWN
  REFERENCE ONLY.

  TO DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
ĸ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Г	6.40	BSC	0.252	BSC	
М	0°	8°	0 °	8 °	

#### **PACKAGE DIMENSIONS**

SOEIAJ-14 **M SUFFIX** CASE 965-01 **ISSUE O** 



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		1.42		0.056

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability, arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free LISA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.